Stuff

Exam 2: Friday 3/7/03

I'll try to keep distributing lecture notes for those people who do come to lecture. I will aim to bring enough each day for those students who are here at the begining of class. If you're not here, too bad. They will no longer be posted on the web. I don't want to enable bad study habits. I will keep any leftovers for those people who have a decent reason for missing lecture. SPICE #S1, due: W, 3/5 hw 12 handout

Note changes in due dates below

HW #13, due: M, 3/3 Ex3.10-12, prob. 3.32, 34, 35

Answers: $3.32 J_0 = 8.64 \times 10^{-8} \text{ A/cm}^3 3.35$:

 $N_D = 9.3 \times 10^{17} / \text{cm}^3$

HW #14, due: F, 3/7 Ex3.13-15 (Note: units of $D_n \& D_n$ are wrong in Ex3.15)

Bipolar Junction Transistor (BJT) basics

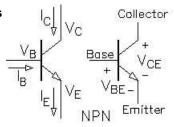
A transistor has three terminals-- the base, the collector, and the emitter. The current flow from the collector to the emitter (through the transistor) is controlled by the current flow from the base to the emitter. A small base current can control a much larger collector current.

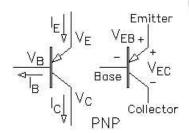
Bipolar junction transistors (BJTs) consist of three layers of doped silicon. The NPN transistor has a thin layer of P-doped silicon sandwiched between two layers of N-doped silicon. Each P-N junction can act like a diode. In fact, this is a fairly good way to check a transistor with an ohmmeter (set to the diode setting).

Collector

The base-emitter junction always acts like a diode, but because the base is very thin, it makes the other junction act like a controlled valve (details to come later).

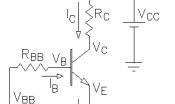
Symbols and conventions

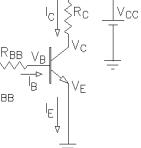




PNP: Replace v_{BE} with v_{EB} and \mathbf{v}_{CE} with \mathbf{v}_{EC} in equations below

outside of the transistor





Modes or regions of operation $(v_{BE} \text{ and } v_{CE} \text{ are approximate})$

$$\begin{array}{lll} & \underline{\text{Cutoff}} \ (\text{off}) & \underline{\text{Active (partially on)}} \\ & v_{BE} < 0.7 \cdot V & \\ & i_{B} = 0 & i_{B} > 0 & \\ & i_{C} = 0 & v_{CE} \ge 0.7 \cdot V & \\ & i_{C} = \beta \cdot i_{B} = \alpha \cdot i_{E} \\ & \text{controlled by the transistor} & \\ \end{array}$$

Saturation (fully on)
$$v_{BE} \sim 0.7 \cdot V$$

$$i_{B} > 0$$

$$v_{CE} = 0.2 \text{ to } 0.7 \cdot V$$

$$i_{C} < \beta \cdot i_{B} \text{ limited by something}$$

Typical transistor curves

